## **LISTING OF CLAIMS:**

The following listing of claims replaces all previous versions and listings of claims in the present application.

- 1. (Withdrawn) A semiconductor device comprising:
- a semiconductor substrate;
- a diffusion structure formed on the semiconductor substrate;
- a trench formed in the diffusion structure; and
- a semiconductor component separated and isolated from surrounding areas thereof in the substrate by the trench, wherein the trench defines a size of the semiconductor component.
  - 2. (Withdrawn) The semiconductor device according to claim 1, further comprising:
  - a plurality of trenches formed in the diffusion structure; and
- a plurality of semiconductor components of a kind separated and isolated from surrounding areas thereof in the substrate by the trenches, wherein the trenches define sizes of the semiconductor components.
- 3. (Withdrawn) The semiconductor device according to claim 1, wherein the semiconductor substrate is a silicon on insulator substrate.
  - 4. (Withdrawn) The semiconductor device according to claim 3, wherein: the silicon on insulator substrate includes an insulating layer and a semiconductor layer;

the semiconductor layer is formed on the insulating layer; and the semiconductor layer has a thickness equal to or less than five micrometers.

- 5. (Withdrawn) The semiconductor device according to claim 1, wherein the trench is filled in with borophosphosilicate glass.
- 6. (Withdrawn) The semiconductor device according to claim 1, wherein the diffusion structure includes a repeated pattern.
- 7. (Withdrawn) The semiconductor device according to claim 1, wherein the diffusion structure includes diffusion regions in rectangular shape arranged in a repeated pattern.
- 8. (Withdrawn) The semiconductor device according to claim 1, wherein the semiconductor component is an analog component for processing an analog signal.
- 9. (Withdrawn) The semiconductor device according to claim 8, wherein the analog component is a bipolar transistor.
- 10. (Withdrawn) The semiconductor device according to claim 1, wherein the semiconductor device is a power component for controlling power supply.
- 11. (Withdrawn) The semiconductor device according to claim 10, wherein the power component is a laterally diffused metal oxide semiconductor transistor.
- 12. (Withdrawn) The semiconductor device according to claim 10, wherein the power component is an insulated gate bipolar transistor.

- 13. (Withdrawn) The semiconductor device according to claim 1, wherein the semiconductor device is a hybrid-IC in which different kinds of semiconductors are integrated in a single chip.
- 14. (Currently amended) A method for manufacturing a semiconductor device that includes a semiconductor component formed on a substrate, comprising:

forming a diffusion structure larger than the semiconductor component in a region of the substrate in which the semiconductor component is formed;

separating a part of the diffusion structure from a surrounding area thereof by the <u>a</u> trench to form the semiconductor component along with defining a size of the semiconductor component; and

connecting a metallization pattern to the semiconductor component.

- 15. (Original) The method according to claim 14, wherein the semiconductor substrate, in a region of which the diffusion structure is formed, is a silicon on insulator substrate.
  - 16. (Original) The method according to claim 15, wherein:

the silicon on insulator substrate includes a semiconductor layer formed on an insulating layer; and

the semiconductor layer is equal to or less than five micrometers.

17. (Original) The method according to claim 14 further comprising filling in the trench with borophosphosilicate glass.

- 18. (Original) The method according to claim 14, wherein the diffusion structure is formed including a repeated pattern in the region.
- 19. (Original) The method according to claim 14, wherein the diffusion structure is formed including diffusion regions shaped in a rectangular.
- 20. (Currently amended) The method according to claim 14, wherein the semiconductor device component formed in the separating step is an analog component for processing an analog signal.
- 21. (Original) The method according to claim 20, wherein the analog component is a bipolar transistor.
- 22. (Currently amended) The method according to claim 14, wherein the semiconductor device component formed in the separating step is a power component for controlling power supply.
- 23. (Withdrawn) The method according to claim 22, wherein the power component is an insulated gate bipolar transistor.
- 24. (Original) The method according to claim 22, wherein the power component is an LDMOS transistor.

- 25. (Original) The method according to claim 14, wherein the semiconductor device manufactured by the method is a hybrid IC including different kinds of semiconductor components integrated into a single chip.
- 26. (Original) A method for manufacturing a semiconductor device that includes a plurality of semiconductor components of a kind in a region of a semiconductor substrate, comprising:

forming a common diffusion structure in the region in which the semiconductor components are formed;

separating parts of the diffusion structure from a surrounding area thereof by trenches to form the semiconductor components along with defining sizes of the semiconductor components; and

connecting metallization patterns to the semiconductor components.

- 27. (Original) The method according to claim 26, wherein the semiconductor substrate, in a region of which the diffusion structure is formed, is a silicon on insulator substrate.
  - 28. (Original) The method according to claim 27, wherein:

the silicon on insulator substrate includes a semiconductor layer formed on an insulating layer; and

the semiconductor layer is equal to or less than five micrometers.

29. (Original) The method according to claim 26, further comprising filling in the trench with borophosphosilicate glass.

- 30. (Original) The method according to claim 26, wherein the diffusion structure is formed including a repeated pattern in the region.
- 31. (Original) The method according to claim 26, wherein the diffusion structure is formed including diffusion regions shaped in a rectangular.
- 32. (Currently amended) The method according to claim 26, wherein the semiconductor device component formed in separating step is an analog component for processing an analog signal.
- 33. (Original) The method according to claim 32, wherein the analog component is a bipolar transistor.
- 34. (Currently amended) The method according to claim 26, wherein the semiconductor device component formed in separating step is a power component for controlling power supply.
- 35. (Withdrawn) The method according to claim 34, wherein the power component is an insulated gate bipolar transistor.
- 36. (Original) The method according to claim 34, wherein the power component is an LDMOS transistor.

- 37. (Currently amended) The method according to claim [2] <u>26</u>, wherein the semiconductor device manufactured by the method is includes a hybrid IC and wherein the plurality of semiconductor components are including different kinds of semiconductor components integrated into a single chip.
- 38. (New) A method for manufacturing a semiconductor device that includes a semiconductor component of a kind formed in a substrate, the method comprising:

forming a diffusion structure including a repeated pattern of diffusion regions common to the kind in an area of the substrate, in which the semiconductor component is to be formed;

separating a part of the diffusion structure from a surrounding area thereof by forming a trench for encircling the part of the diffusion structure including at least a part of the repeated pattern of diffusion regions so as to define the semiconductor component including a predetermined size thereof, and to insulate the semiconductor component from the surrounding area after forming the diffusion structure; and

connecting a metallization pattern to the semiconductor component.

39. (New) A method for manufacturing a semiconductor device that includes a first semiconductor component and a second semiconductor component formed in a substrate, the method comprising:

forming a first diffusion structure including a first repeated pattern of first diffusion regions common to a first kind in a first area of the substrate in which the first semiconductor component is to be formed;

forming a second diffusion structure including a second repeated pattern of second diffusion regions common to a second kind in a second area of the substrate in which the second semiconductor component is to be formed;

separating a part of the first diffusion structure from a surrounding area thereof by forming a first closed trench for encircling at least a part of the first diffusion structure including at least a part of the first repeated pattern of the first diffusion regions to define the first semiconductor component of the first kind including a first predetermined size thereof, and to insulate the first semiconductor component from the surrounding area after forming the first diffusion structure and by connecting a first metallization pattern to the first semiconductor component; and

separating a part of the second diffusion structure from the surrounding area by forming a second closed trench for encircling at least a part of the second diffusion structure including at least a part of the second repeated pattern of the second diffusion regions to define the second semiconductor component of the second kind including a second predetermined size thereof, and to insulate the second semiconductor component from the surrounding area after forming the second diffusion structure and by connecting a second metallization pattern to the second semiconductor component.

40. (New) A method for manufacturing a semiconductor device that includes a semiconductor component of one of a plurality of kinds formed in a substrate, the method comprising:

forming a plurality of diffusion structures associated with the plurality of kinds, each of the plurality of diffusion structures including a repeated pattern of diffusion regions common to Serial No. 10/656,326

one of the plurality of kinds, in an area of the substrate, in which the semiconductor component of the one of the plurality of kinds is formed;

separating a part of one of the plurality of diffusion structures from a surrounding area thereof by forming a trench, which encircles the part of the one of the plurality of diffusion structures including at least a part of the repeated pattern of the diffusion regions to define the semiconductor component of the one of the plurality of kinds including a predetermined size thereof, and to insulate the semiconductor component from the surrounding area, after forming the diffusion structures; and

connecting metallization patterns to the semiconductor component.